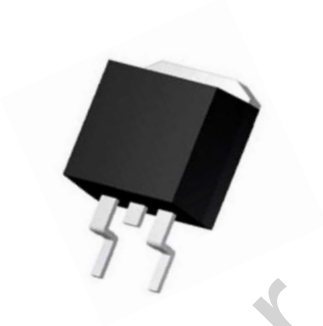
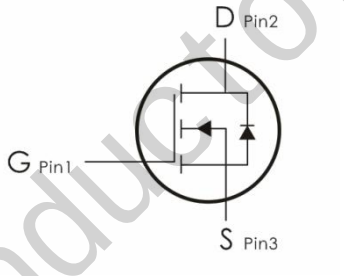
Features:

- ☐ Low Intrinsic Capacitances.
- ☐ Excellent Switching Characteristics.
- ☐ Extended Safe Operating Area.
- ☐ Unrivalled Gate Charge :Qg=60nC (Typ.).
- ☐ BVDSS=100V,I_D=100A
- ☐ R_{DS}(on) : 0.012Ω (Max) @V_G=10V
- ☐ 100% Avalanche Tested





Absolute Maximum Ratings (T_A=25°C unless otherwise noted)

Symbol	Parameter		Maximum	Unit
V_{DSS}	Drain-to-Source Voltage		100	V
V_{GSS}	Gate-to-Source Voltage		±25	V
I_D[3]	Continuous Drain Current	T_C=25°C	100	A
		T_C=100°C	51	
I_{DP}[4]	Pulsed Drain Current	T_C=25°C	219	
IAS[5]	Avalanche Current		30	
EAS[5]	Avalanche energy		225	mJ
PD	Maximum Power Dissipation	T_C=25°C	166	W
		T_C=100°C	83	
T_J, T_{STG}	Junction & Storage Temperature Range		-55~175	°C

Thermal Characteristics

Symbol	Parameter	Typical	Unit
Rθjc	Thermal Resistance-Junction to Case	0.9	°C/W
Rθja	Thermal Resistance-Junction to Ambient	62.5	

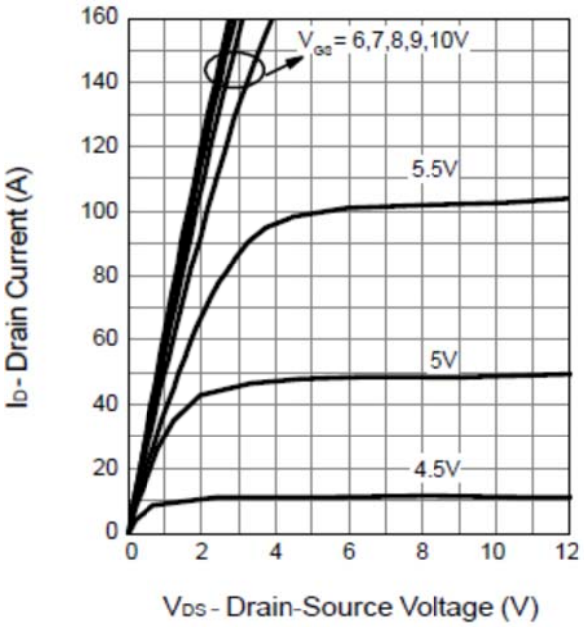
Electrical Characteristics (T_A=25°C unless otherwise noted)

Symbol	Parameter	Test Conditions	Min.	Typ	Max.	Unit
Static Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V,I_D=250uA	100	—	—	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=80V,V_{GS}=0V	—	—	1	uA
		T_J=125°C	—	—	20	
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS},I_D=250uA	2	3	4	V
I_{GSS}	Gate Leakage Current	V_{GS}=±25V, V_{DS}=0V	—	—	±100	nA
$R_{DS(on)}$[1]	Drain-Source On-Resistance	V_{GS}=10V, I_D=50A	—	10	12	mΩ
			—	—	—	
Diode Characteristics						
V_{SD}[1]	Diode Forward Voltage	I_{SD}=50A,V_{GS}=0V	—	—	1.3	V
I_S[3]	Diode Continuous Forward Current		—	—	100	A
t_{rr}	Reverse Recovery Time	I_F=50A, dI/dt=100A/us	—	46	—	nS
Q_{rr}	Reverse Recovery Charge		—	86	—	nC
Dynamic Characteristics[2]						
R_G	Gate Resistance	V_{GS}=0V, V_{DS}=0V, Frequency=1MHz	—	1.2	—	Ω
C_{iss}	Input Capacitance	V_{GS}=0V, V_{DS}=25V Frequency=1MHz	—	2946	—	pF
C_{oss}	Output Capacitance		—	339	—	
C_{rss}	Reverse Transfer Capacitance		—	179	—	
$t_{d(on)}$	Turn-On Delay Time	V_{DD}=50V,I_D=30A, V_{GS}=10V,R_G=6.8Ω	—	15	—	nS
t_r	Rise Time		—	108	—	
$t_{d(off)}$	Turn-Off Delay Time		—	51	—	
t_f	Fall Time		—	59	—	
Gate Charge Characteristics[2]						
Q_g	Total Gate Charge	V_{DS}=50V,V_{GS}=10V I_D=30A	—	60	—	nC
Q_{gs}	Gate-to-Source Charge		—	13.7	—	
Q_{gd}	Gate-to-Drain Charge		—	22.8	—	

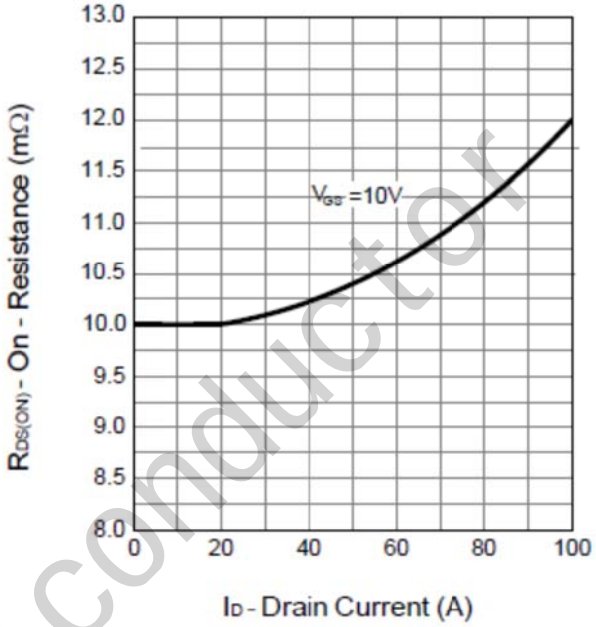
Note: 1: Pulse test; pulse width ≦ 300us, duty cycle ≦ 2%.
2: Guaranteed by design, not subject to production testing.
3: Package limitation current is 55A.
4: Repetitive rating, pulse width limited by max junction temperature.
5: Starting TJ = 25°C,L = 0.5mH,IAS = 30A.

Typical Characteristics

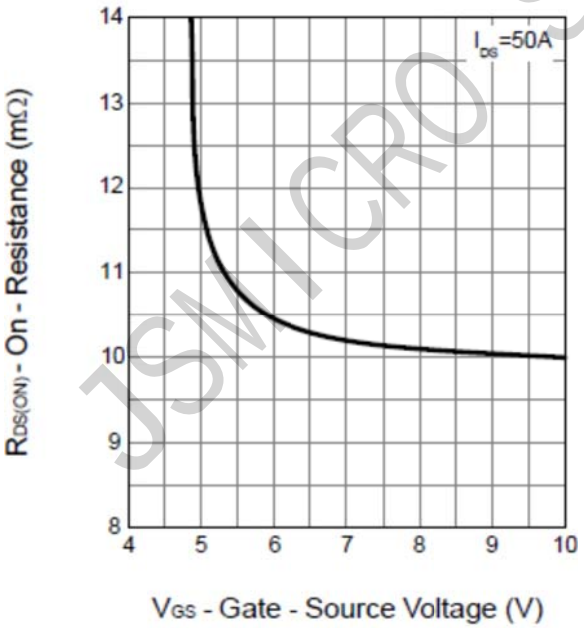
Output Characteristics



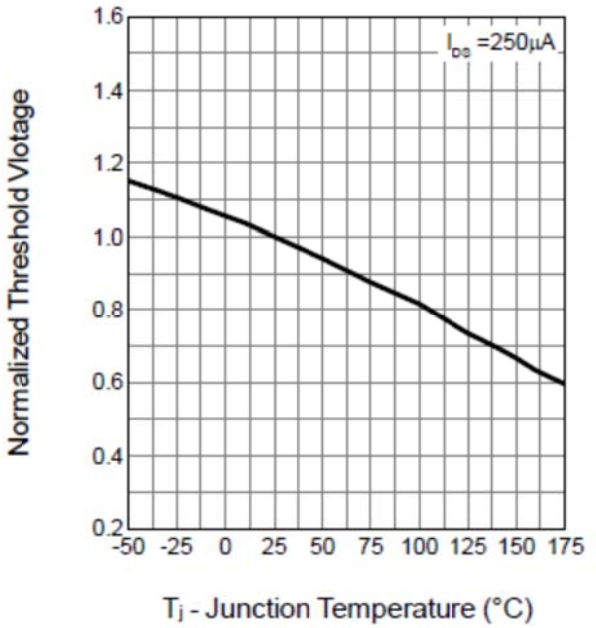
Drain-Source On Resistance



Drain-Source On Resistance

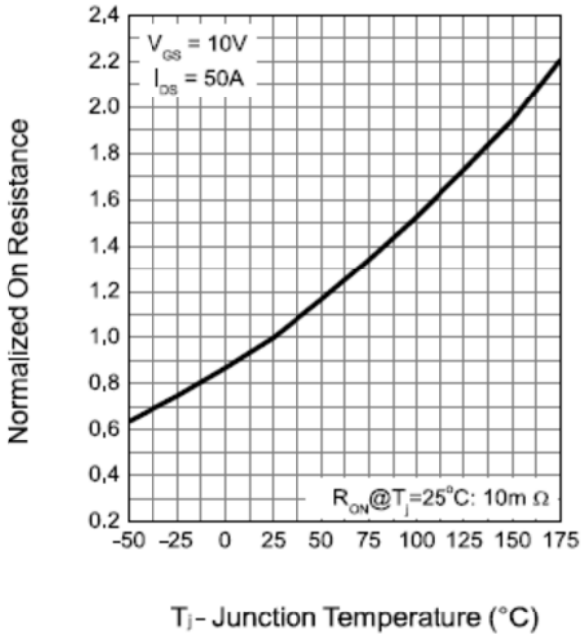


Gate Threshold Voltage

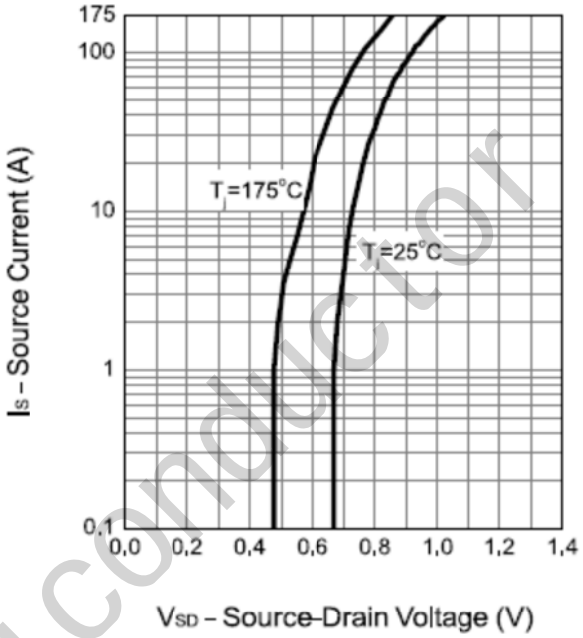


Typical Characteristics (Continued)

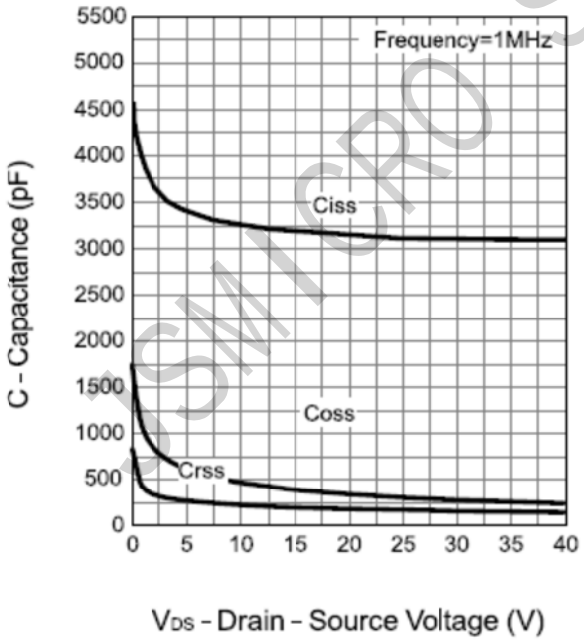
Drain-Source On Resistance



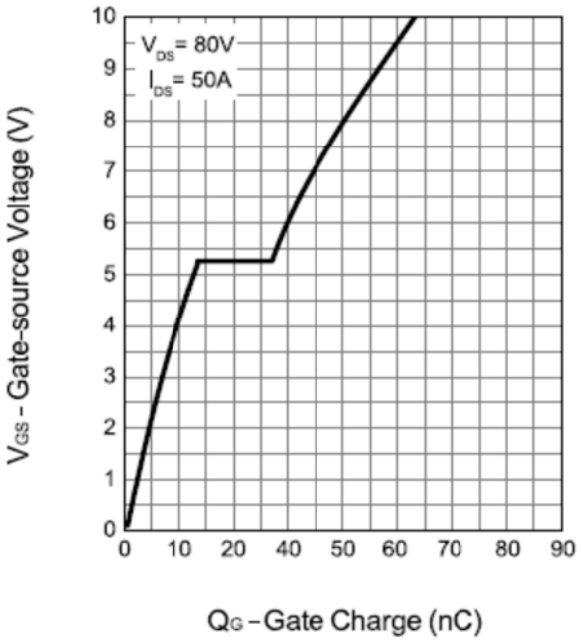
Source-Drain Diode Forward



Capacitance

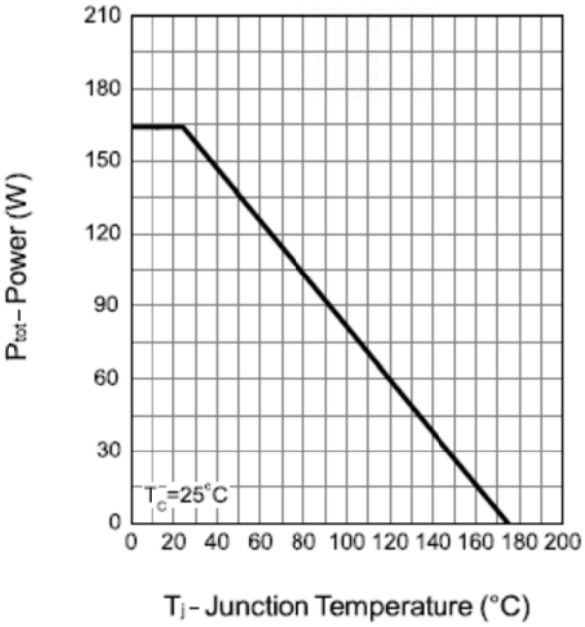


Gate Charge

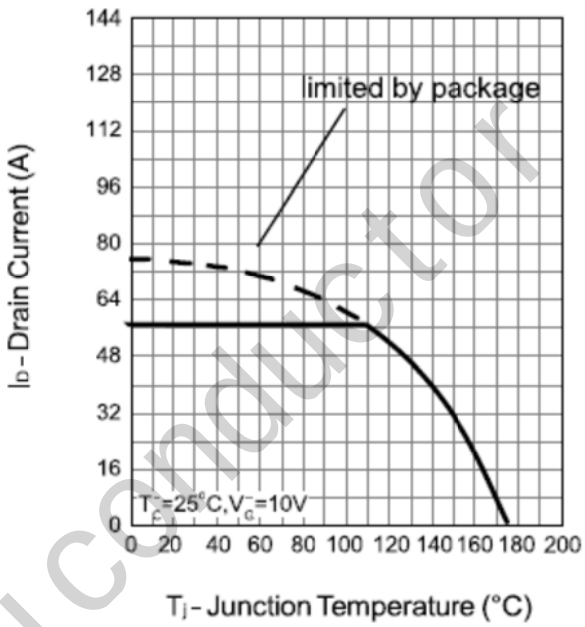


Typical Characteristics (Continued)

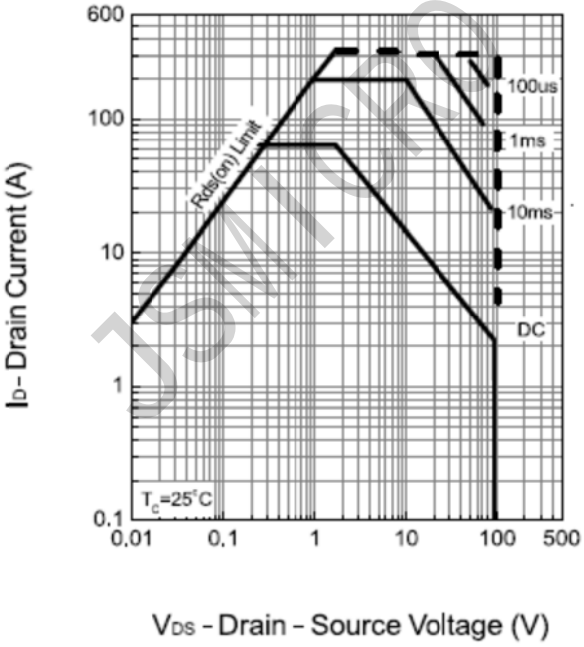
Power Dissipation



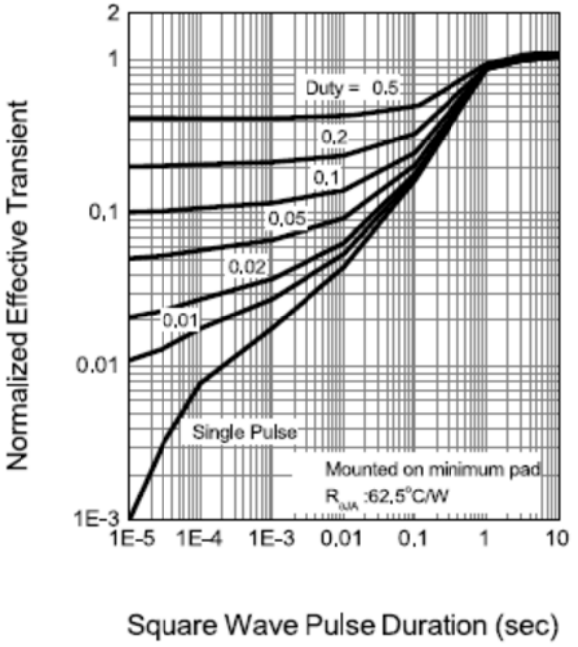
Drain Current



Safe Operation Area



Thermal Transient Impedance



外形尺寸图 / Package Dimensions

TO-263

Unit: mm